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INFORMATION REPORT

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25X1

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1. Interest in East German semi-conductor research and development, and in particular in the development of transistors, on the part of the USSR and the satellite countries, has been great. The Soviets initiated transistor development at VEB Werk fuer Fernmeldewesen (formerly OSW), in Berlin-Oberschoeneweide, and they also kept themselves informed on the progress of transistor development at VEB Werk fuer Bauelemente der Nachrichtentechnik, Carl von Ossietzky (formerly Dralowid) in Peltow. 25X1
2. In April 1953, the East German government issued an order (Regierungs-beschluss UP152/IV) concerning the cooperation of East Germany with the satellite countries in the field of the development of semi-conductors. WTZ (Department for Scientific-Technical Cooperation), of the State Planning Commission, issued instructions for carrying out this order. 25X1 According to the terms of these instructions, two Hungarian delegates were authorized to visit the Dralowid plant, the Academy Institute for Research on the Physics of Solids, and the OSW plant, in order to obtain information on the development of transistors, the methods of purification of germanium, and on the development of thermistors. It was furthermore stipulated that copies of the documentary material pertaining to the development of transistors and thermistors was to be made available to the Hungarian delegates if they desired it. The management of the Dralowid plant in particular was ordered to comply with any demand of the Hungarian delegates. For unknown reasons, however, Hungary had failed to send the delegates to East Germany in November 1954. 25X1 their visit was deferred but was cancelled.
3. In September 1954, seven Czechoslovak technicians visited East Germany under the auspices of WTZ and made extended studies on the development of germanium and silicon diodes and of transistors in the Dralowid and OSW plants, the Academy Institute for Research on the Physics of Solids in Berlin-Buch, and in the Academy Institute for Oscillation Research (Heinrich-Hertz-Institut) in Berlin-Adlershof². In October 1954, a Czech semi-conductor specialist, Matthias (fnu), arrived for a four-week visit in East Germany and made studies in the Dralowid and OSW plants and the Academy Institute for Research on the Physics of Solids in Berlin-Buch³. This visit was also organized by WTZ.

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-2-

- 4- In November 1954, a young Bulgarian technician, name unknown, arrived at the Academy Institute for Research on the Physics of Solids, in Berlin-Buch, for a prolonged stay; his purpose was to study semi-conductor and transistor research, His visit too, was sponsored by WTZ.

25X1

Comment: This Institute is not actually engaged in transistor development. It is, however, carrying out research on semi-conductors generally and on germanium in particular. The Czech visitors were mostly interested in the use of germanium and silicon diodes for purposes of high-frequency technology. The Institute works with germanium and silicon, diodes procured from the OSW plant.

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25X1

-2-

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